

In the Claims:

1. (Previously presented) An aqueous chemical mechanical planarizing composition comprising:
 - an oxidizer for promoting barrier removal;
 - an abrasive;
 - an inhibitor for decreasing removal of a metal interconnect; and
 - water soluble polymaleic acid and wherein the chemical mechanical planarizing composition has a pH of less than 4 adjusted with an inorganic pH adjusting agent, the inorganic pH adjusting agent being an acid; and a tantalum nitride removal rate of at least eighty percent of copper removal rate at a pad pressure of 13.8 kPa.
2. (Previously presented) The composition of Claim 1, wherein the polymaleic acid comprises a homopolymer or a copolymer.
3. Cancelled.
4. (Previously presented) The composition of Claim 1, having a pH of 1.5 to less than 4.
5. (Currently amended) An aqueous chemical mechanical planarizing composition comprising:
 - 0.05 to 15 wt% abrasive;
 - 0.1 to 10 wt% oxidizing agent;
 - 0.0025 to 2 wt% of benzotriazole; and
 - 0.01 to 5 wt% of water soluble polymaleic acid, and wherein the pH of the chemical mechanical planarizing composition is less than 4 adjusted with an inorganic pH adjusting agent, the inorganic pH adjusting agent including an acid selected from nitric acid, sulfuric acid, hydrochloric acid and phosphoric acid; and a tantalum nitride removal rate of at least ninety eighty percent of copper removal rate at a pad pressure of 13.8 kPa.
6. (Previously presented) The composition of Claim 5, wherein the polymaleic acid comprises a homopolymer or a copolymer.

7. Cancelled.

8. (Withdrawn) A method for planarizing a semiconductor wafer comprising:

applying an aqueous chemical mechanical planarizing composition to the wafer, wherein the composition comprises water soluble polymaleic acid; an abrasive; an oxidizer for promoting barrier removal; and a corrosion inhibitor for limiting removal of the interconnect metal, wherein the chemical mechanical planarizing composition has a pH of less than 4 adjusted with an inorganic pH adjusting agent, the inorganic pH adjusting agent being an acid; and

polishing the semiconductor wafer, wherein the chemical mechanical planarizing composition has a tantalum nitride removal rate of at least eighty percent of copper removal rate at a pad pressure of 13.8 kPa.

9. (Withdrawn) A method for planarizing a semiconductor wafer comprising:

applying an aqueous chemical mechanical planarizing composition to the wafer, wherein the composition comprises 0.05 to 15 wt% abrasive; 0.1 to 10 wt% oxidizing agent; and 0.0025 to 2 wt% of benzotriazole; and 0.01 to 5 wt% of water soluble polymaleic acid, and wherein the pH of the chemical mechanical planarizing composition is less than 4 adjusted with an inorganic pH adjusting agent, the inorganic pH adjusting agent including an acid selected from nitric acid, sulfuric acid, hydrochloric acid and phosphoric acid; and

polishing the semiconductor wafer at a pad pressure less than or equal to about 21.7 kPa, wherein the chemical mechanical planarizing composition has a tantalum nitride to copper selectivity of at least eighty percent of copper removal rate.

10. Cancelled.